

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	61981	(nitride or nitridat\$4 or N2 or N?sub\$2 or nitrogen or nitridiz\$4) same (thickness or angstrom or nm or nanometer or ".ang.")	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2003/04/30 14:34
2	BRS	L8	59135	(oxidat\$4 or oxidiz\$4 or thermal-oxid\$6) same (thickness or angstrom or nm or nanometer or ".ang.")	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2003/04/30 14:45
3	BRS	L15	11629	1 and 8	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2003/04/30 14:36
4	BRS	L22	8299	15 and semiconductor	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2003/04/30 14:38
7	BRS	L43	2866	22 and ((N or nitrogen or N?su\$3 or nitrogen-contain\$4 or nitrogen-compris\$4) near20 (dispers\$4 or migrat\$4 or immigrat\$4 or mov\$4 or concentration or distribut\$4))	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2003/04/30 14:44

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L64	10152	(oxidat\$4 or oxidiz\$4 or thermal-oxid\$6 or oxide) near20 ((N or nitrogen or N?su\$3 or nitrogen-contain\$4 or nitrogen-compris\$4) near20 (dispers4 or migrat\$4 or immigrat\$4 or mov\$4 or concentration or distribut\$4))	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2003/04/30 15:36
12	BRS	L78	687	64 and 43	USPAT; US-PG PUB; EPO; JPO; DERW ENT; IBM_TD B	2003/04/30 15:46